DL PACKAGE

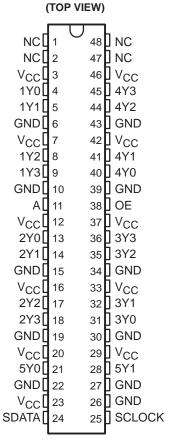
SCAS614 - SEPTEMBER 1998

- High-Speed, Low-Skew 1-to-18 Clock Buffer for Synchronous DRAM (SDRAM) Clock Buffering Applications
- Output Skew, t_{sk(o)}, Less Than 250 ps
- Pulse Skew, t_{sk(p)}, Less Than 500 ps
- Supports up to Four Unbuffered SDRAM Dual Inline Memory Modules (DIMMs)
- I²C Serial Interface Provides Individual Enable Control for Each Output
- Operates at 3.3 V
- Distributed V_{CC} and Ground Pins Reduce Switching Noise
- 100-MHz Operation
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015
- Packaged in 48-Pin Shrink Small Outline (DL) Package

description

The CDC318A is a high-performance clock buffer designed to distribute high-speed clocks in PC applications. This device distributes one input (A) to 18 outputs (Y) with minimum skew for clock distribution. The CDC318A operates from a 3.3-V power supply. It is characterized for operation from 0°C to 70°C.

This device has been designed with consideration for optimized EMI performance. Depending on the application layout, damping resistors in series to the clock outputs (like proposed in the PC100 specification) may not be needed in most cases.



NC - No internal connection

The device provides a standard mode (100K-bits/s) I²C serial interface for device control. The implementation is as a slave/receiver. The device address is specified in the I²C device address table. Both of the I²C inputs (SDATA and SCLOCK) are 5-V tolerant and provide integrated pullup resistors (typically 140 k Ω).

Three 8-bit I²C registers provide individual enable control for each of the outputs. All outputs default to enabled at powerup. Each output can be placed in a disabled mode with a low-level output when a low-level control bit is written to the control register. The registers are write only and must be accessed in sequential order (i.e., random access of the registers is not supported).

The CDC318A provides 3-state outputs for testing and debugging purposes. The outputs can be placed in a high-impedance state via the output-enable (OE) input. When OE is high, all outputs are in the operational state. When OE is low, the outputs are placed in a high-impedance state. OE provides an integrated pullup resistor.



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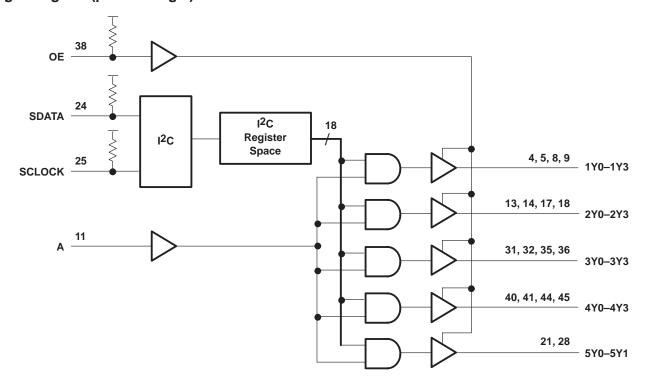


FUNCTION TABLE

| INPUTS | | OUTPUTS | | | | |
|--------|---|---------|---------|---------|---------|---------|
| OE | Α | 1Y0-1Y3 | 2Y0-2Y3 | 3Y0-3Y3 | 4Y0-4Y3 | 5Y0-5Y1 |
| L | Χ | Hi-Z | Hi-Z | Hi-Z | Hi-Z | Hi-Z |
| Н | L | L | L | L | L | L |
| Н | Н | н† | н† | н† | н† | н† |

[†] The function table assumes that all outputs are enabled via the appropriate I²C configuration register bit. If the output is disabled via the appropriate configuration bit, then the output is driven to a low state, regardless of the state of the A input.

logic diagram (positive logic)





Terminal Functions

| | TERMINAL | 1/0 | DESCRIPTION |
|---------|--|-----|--|
| NAME | NO. | I/O | DESCRIPTION |
| 1Y0-1Y3 | 4, 5, 8, 9 | 0 | 3.3-V SDRAM byte 0 clock outputs |
| 2Y0-2Y3 | 13, 14, 17, 18 | 0 | 3.3-V SDRAM byte 1 clock outputs |
| 3Y0-3Y3 | 31, 32, 35, 36 | 0 | 3.3-V SDRAM byte 2 clock outputs |
| 4Y0-4Y3 | 40, 41, 44, 45 | 0 | 3.3-V SDRAM byte 3 clock outputs |
| 5Y0-5Y1 | 21, 28 | 0 | 3.3-V clock outputs provided for feedback control of external phase-locked loops (PLLs) |
| А | 11 | I | Clock input |
| OE | 38 | I | Output enable. When asserted, OE puts all outputs in a high-impedance state. A nominal 140 -k Ω pullup resistor is internally integrated. |
| SCLOCK | 25 | I | I ² C serial clock input. A nominal 140-kΩ pullup resistor is internally integrated. |
| SDATA | 24 | I/O | Bidirectional I ² C serial data input/output. A nominal 140-k Ω pullup resistor is internally integrated. |
| GND | 6, 10, 15, 19, 22, 26, 27, 30, 34, 39, 43 | | Ground |
| NC | 1, 2, 47, 48 | | No internal connection. Reserved for future use. |
| VCC | 3, 7, 12, 16, 20, 23, 29, 33, 37, 42, 46 | | 3.3-V power supply |

I²C DEVICE ADDRESS

| A7 | A6 | A5 | A4 | А3 | A2 | A1 | A0 (R/W) |
|----|----|----|----|----|----|----|----------|
| Н | Н | L | Н | L | L | Н | _ |

I²C BYTE 0-BIT DEFINITION[†]

| BIT | DEFINITION | DEFAULT VALUE |
|-----|---------------------|---------------|
| 7 | 2Y3 enable (pin 18) | Н |
| 6 | 2Y2 enable (pin 17) | Н |
| 5 | 2Y1 enable (pin 14) | Н |
| 4 | 2Y0 enable (pin 13) | Н |
| 3 | 1Y3 enable (pin 9) | Н |
| 2 | 1Y2 enable (pin 8) | Н |
| 1 | 1Y1 enable (pin 5) | Н |
| 0 | 1Y0 enable (pin 4) | Н |

[†]When the value of the bit is high, the output is enabled. When the value of the bit is low, the output is forced to a low state. The default value of all bits is high.



I²C BYTE 1-BIT DEFINITION[†]

| BIT | DEFINITION | DEFAULT VALUE |
|-----|---------------------|---------------|
| 7 | 4Y3 enable (pin 45) | Н |
| 6 | 4Y2 enable (pin 44) | Н |
| 5 | 4Y1 enable (pin 41) | Н |
| 4 | 4Y0 enable (pin 40) | Н |
| 3 | 3Y3 enable (pin 36) | Н |
| 2 | 3Y2 enable (pin 35) | Н |
| 1 | 3Y1 enable (pin 32) | Н |
| 0 | 3Y0 enable (pin 31) | Н |

[†]When the value of the bit is high, the output is enabled. When the value of the bit is low, the output is forced to a low state. The default value of all bits is high.

I²C BYTE 2-BIT DEFINITION[†]

| BIT | DEFINITION | DEFAULT VALUE |
|-----|---------------------|---------------|
| 7 | 5Y1 enable (pin 28) | Н |
| 6 | 5Y0 enable (pin 21) | Н |
| 5 | Reserved | Н |
| 4 | Reserved | Н |
| 3 | Reserved | Н |
| 2 | Reserved | Н |
| 1 | Reserved | Н |
| 0 | Reserved | Н |

 $^{^{\}dagger}$ When the value of the bit is high, the output is enabled. When the value of the bit is low, the output is forced to a low state. The default value of all bits is high.



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

| Supply voltage range, V _{CC} | –0.5 V to 4.6 V |
|---|--------------------------------|
| Input voltage range, V _I (see Note 1) | –0.5 V to 4.6 V |
| Input voltage range, V _I (SCLOCK, SDATA) (see Note 1) | –0.5 V to 6.5 V |
| Output voltage range, V _O (SDATA) (see Note 1) | –0.5 V to 6.5 V |
| Voltage range applied to any output in the high or power-off state, V _O −0.5 | 5 V to V_{CC} +0.5 V |
| Current into any output in the low state (except SDATA), IO | 48 mA |
| Current into SDATA in the low state, I _O | |
| Input clamp current, I _{IK} (V _I < 0) (SCLOCK) | –50 mA |
| Output clamp current, I _{OK} (V _O < 0) (SDATA) | –50 mA |
| Package thermal impedance, θ _{JA} (see Notes 2 and 3) | |
| Storage temperature range, T _{stq} | |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for through-hole packages, which use a trace length of zero. The absolute maximum power dissipation allowed at T_A = 55°C (in still air) is 1.2 W.
 - 3. Thermal impedance (ΘJA) can be considerably lower if the device is soldered on the PCB board with a copper layer underneath the package. A simulation on a PCB board (3 in. × 3 in.) with two internal copper planes (1 oz. cu, 0.036 mm thick) and 0.071 mm cu (202) in area underneath the package, resulted in ΘJA = 60°C/W. This would allow 1.2 W total power dissipation at TA = 70°C.

recommended operating conditions (see Note 4)

| | | | MIN | TYP | MAX | UNIT |
|------------------------|-------------------------------------|-------------------------------|-------|-----|----------------------|------|
| Vcc | 3.3-V core supply voltage | | 3.135 | | 3.465 | V |
| | | A, OE | 2 | | V _{CC} +0.3 | V |
| VIH | High-level input voltage | SDATA, SCLOCK (see Note 3) | 2.2 | | 5.5 | V |
| | | A, OE | -0.3 | | 0.8 | V |
| VIL | Low-level input voltage | SDATA, SCLOCK (see Note 3) | 0 | | 1.04 | V |
| ІОН | High-level output current | Y outputs | | | -36 | mA |
| loL | Low-level output current | Y outputs | | | 24 | mA |
| rį | Input resistance to V _{CC} | SDATA, SCLOCK (see Note 3) | | 140 | | kΩ |
| f(SCL) | SCLOCK frequency | | | | 100 | kHz |
| t(BUS) | Bus free time | | 4.7 | | | μs |
| t _{su(START)} | START setup time | | 4.7 | | | μs |
| th(START) | START hold time | | 4 | | | μs |
| tw(SCLL) | SCLOCK low pulse duration | | 4.7 | | | μs |
| tw(SCLH) | SCLOCK high pulse duration | | 4 | | | μs |
| ^t r(SDATA) | SDATA input rise time | | | | 1000 | ns |
| tf(SDATA) | SDATA input fall time | | | | 300 | ns |
| t _{su(SDATA)} | SDATA setup time | | 250 | | | ns |
| th(SDATA) | SDATA hold time | | 20 | | | ns |
| t _{su(STOP)} | STOP setup time | | 4 | | | μs |
| TA | Operating free-air temperature | | 0 | | 70 | °C |

NOTE 4: The CMOS-level inputs fall within these limits: V_{IH} min = $0.7 \times V_{CC}$ and V_{IL} max = $0.3 \times V_{CC}$.



CDC318A 1-LINE TO 18-LINE CLOCK DRIVER WITH I²C CONTROL INTERFACE SCAS614 - SEPTEMBER 1998

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | | | TEST CON | IDITIONS | MIN | TYP | MAX | UNIT |
|------------------|------------------------------------|---------------|--|-------------------------------|----------------------------|-----|------|------|
| VIK | Input clamp voltage | | V _{CC} = 3.135 V, | I _I = -18 mA | | | -1.2 | V |
| Vон | High-level output voltage | Y outputs | V _{CC} = Min to Max, | $I_{OH} = -1 \text{ mA}$ | V _{CC} – 0.1 V | | | V |
| | | | $V_{CC} = 3.135 \text{ V},$ | $I_{OH} = -36 \text{ mA}$ | 2.4 | | | |
| | | Y outputs | V _{CC} = Min to Max, | I _{OL} = 1 mA | | | 0.1 | |
| VOL | Low-level output voltage | Toutputs | $V_{CC} = 3.135 \text{ V},$ | I _{OL} = 24 mA | | | 0.4 | V |
| VOL | Low-level output voltage | SDATA | V _{CC} = 3.135 V | $I_{OL} = 3 \text{ mA}$ | | | 0.4 | V |
| | | SDATA | VCC = 3.135 V | I _{OL} = 6 mA | | | 0.6 | |
| | | SDATA | V _{CC} = 3.135 V, | $V_O = V_{CC} MAX$ | | | 20 | μΑ |
| lou | High lovel output current | | $V_{CC} = 3.135 \text{ V},$ | V _O = 2 V | -54 | | -126 | |
| ЮН | High-level output current | Y outputs | $V_{CC} = 3.3 \text{ V},$ | V _O = 1.65 V | | -92 | | mA |
| | | | V _{CC} = 3.465 V, | V _O = 3.135 V | -21 | | -46 | |
| | | | V _{CC} = 3.135 V, | V _O = 1 V | 49 | | 118 | |
| IOL | Low-level output current | Y outputs | V _{CC} = 3.3 V, | V _O = 1.65 V | | 93 | | mA |
| | | | V _{CC} = 3.465 V, | V _O = 0.4 V | 24 | | 53 | |
| | | А | | | | | 5 | |
| lін | High-level input current | OE | V _{CC} = 3.465 V, | $V_I = V_{CC}$ | | | 20 | μА |
| | | SCLOCK, SDATA | | | | | 20 | |
| | | А | | | | | -5 | |
| Ι _Ι L | Low-level input current | OE | V _{CC} = 3.465 V, | $V_I = GND$ | -10 | | -50 | μА |
| | | SCLOCK, SDATA | | | -10 | | -50 | |
| loz | High-impedance-state outp | ut current | V _{CC} = 3.465 V, | V _O = 3.465 V or 0 | | | ±10 | μΑ |
| l _{off} | Off-state current | SCLOCK, SDATA | $V_{CC} = 0$, | V _I = 0 V to 5.5 V | | | 50 | μΑ |
| Icc | Supply current | | V _{CC} = 3.465 V, | I _O = 0 | | 0.2 | 0.5 | mA |
| ΔlCC | Change in supply current | | $V_{CC} = 3.135 \text{ V to } 3.46$ One input at $V_{CC} = 0.4$ All other inputs at V_{CC} | 6 V, | | | 500 | μΑ |
| | Dynamic I _{CC} at 100 MHz | | V _{CC} = 3.465 V, | C _L = 20 pF, | | 230 | | mA |
| Cl | Input capacitance | | $V_I = V_{CC}$ or GND, | V _{CC} = 3.3 V | | 4 | | pF |
| СО | Output capacitance | | $V_O = V_{CC}$ or GND, | V _{CC} = 3.3 V | | 6 | | pF |
| C _{I/O} | SDATA I/O capacitance | | $V_{I/O} = V_{CC}$ or GND, | V _{CC} = 3.3 V | | 7 | | pF |



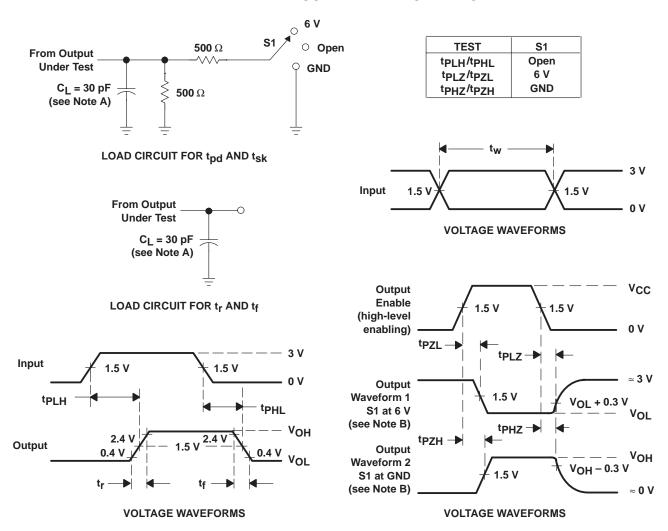
switching characteristics over recommended operating conditions

| | PARAMETER | | | то | TEST CONDITIONS | MIN | MAX | UNIT |
|---------------------|--|------------|---------|----------------|---|-----|-----|------|
| | | | А | Υ | | 1.2 | 4.5 | ns |
| ^t PLH | Low-to-high level propagation delay time | | SCLOCK↓ | SDATA valid | $V_{CC} = 3.3 \text{ V} \pm 0.165 \text{ V},$ See Figure 3 | | 2 | μs |
| ^t PLH | Low-to-high level propagation of | lelay time | SDATA↑ | Υ | $V_{CC} = 3.3 \text{ V} \pm 0.165 \text{ V},$ See Figure 3 | | 150 | ns |
| | | | А | Υ | | 1.2 | 4.5 | ns |
| ^t PHL | High-to-low level propagation delay time | | SCLOCK↓ | SDATA valid | V _{CC} = 3.3 V ±0.165 V, See Figure 3 | | 2 | μs |
| ^t PHL | High-to-low level propagation d | elay time | SDATA↑ | Υ | $V_{CC} = 3.3 \text{ V} \pm 0.165 \text{ V},$ See Figure 3 | | 150 | ns |
| ^t PZH | Enable time to the high level | | OE | Y | | 1 | 7 | |
| ^t PZL | Enable time to the low level | |] | • | | 1 | 7 | ns |
| ^t PHZ | Disable time from the high level | | OE | Y | | 1 | 7 | ns |
| ^t PLZ | Disable time from the low level | |] | r | | 1 | 7 | 115 |
| tsk(o) | Skew time | | А | Υ | | | 250 | ps |
| ^t sk(p) | Skew time | | А | Υ | | | 500 | ps |
| ^t sk(pr) | Skew time | | А | Υ | | | 1 | ns |
| t _r | Rise time | | | Υ | | 0.5 | 2.2 | ns |
| + | Rise time (see Note 5 and | SDATA | | | C _L = 10 pF | 6 | | ns |
| t _r | Figure 3) | SDAIA | | | $C_L = 400 \text{ pF}$ | | 950 | 115 |
| t _f | Fall time | | | Υ | | 0.5 | 2.3 | ns |
| +. | Fall time (see Note 5 and | SDATA | | | C _L = 10 pF | 20 | | ns |
| tf | Figure 3) | SDATA | | | C _L = 400 pF | | 250 | HS |

NOTE 5: This parameter has a lower limit than BUS specification. This allows use of series resistors for current spike protection.



PARAMETER MEASUREMENT INFORMATION



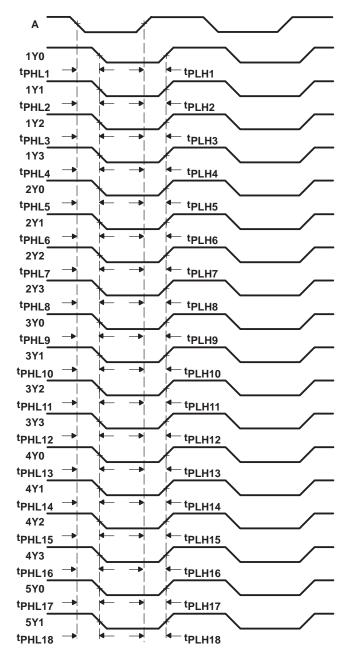
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION



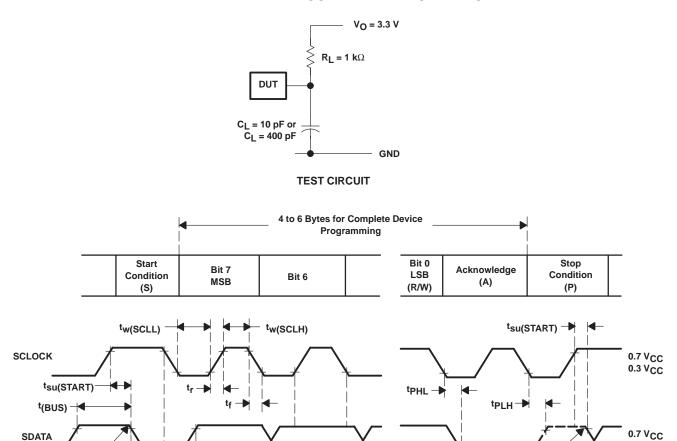
NOTES: A. Output skew, $t_{Sk(O)}$, is calculated as the greater of:

- The difference between the fastest and slowest of tpLHn (n = 1:18)
- The difference between the fastest and slowest of t_{PHLn} (n = 1:18)
- B. Pulse skew, $t_{Sk(p)}$, is calculated as the greater of $|t_{PLHn} t_{PHLn}|$ (n = 1:18)
- C. Process skew, tsk(pr), is calculated as the greater of:
 - The difference between the fastest and slowest of tpLHn (n = 1:18) across multiple devices under identical operating conditions
 - $\ \, \text{The difference between the fastest and slowest of } \\ t_{PHLn} \, (n = 1:18) \, \text{across multiple devices under identical operating conditions} \\$

Figure 2. Waveforms for Calculation of $t_{sk(o)}$, $t_{sk(p)}$, $t_{sk(pr)}$



PARAMETER MEASUREMENT INFORMATION



VOLTAGE WAVEFORMS

⁻ ^th(SDATA)

Repeat Start

(see Note A)

Condition

tr(SDATA)

tsu(SDATA) -

0.3 V_{CC}

t_{su(STOP)}

Stop Condition

| BYTE | DESCRIPTION |
|------|-----------------------------------|
| 1 | I ² C address |
| 2 | Command (dummy value, ignored) |
| 3 | Byte count (dummy value, ignored) |
| 4 | I ² C data byte 0 |
| 5 | I ² C data byte 1 |
| 6 | I ² C data byte 2 |

NOTES: A. The repeat start condition is not supported.

tf(SDATA)

th(START)

Start or

Repeat Start Condition

B. All input pulses are supplied by generators having the following characteristics: PRR \leq 100 kHz, Z_O = 50 Ω , $t_f \geq$ 10 ns. $t_f \geq$ 10 ns.

Figure 3. Propagation Delay Times, tr and tf

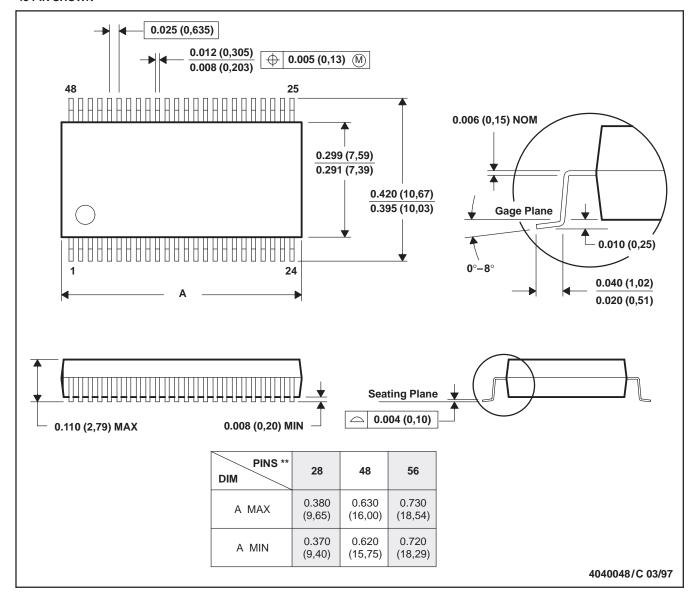


MECHANICAL INFORMATION

DL (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PIN SHOWN



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MO-118

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